

# Dual Complementary General Purpose Transistor

## NST847BPDP6T5G

The NST847BPDP6T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-963 six-leaded surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

### Features

- $h_{FE}$ , 200–450
- Low  $V_{CE(sat)}$ ,  $\leq 0.3$  V
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- This is a Pb-Free Device

### MAXIMUM RATINGS

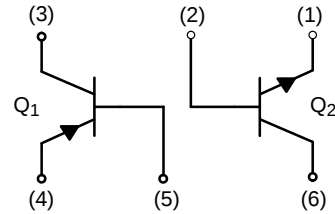
| Rating                         | Symbol    | Value               | Unit |
|--------------------------------|-----------|---------------------|------|
| Collector - Emitter Voltage    | $V_{CEO}$ | 45                  | Vdc  |
| Collector - Base Voltage       | $V_{CBO}$ | 50                  | Vdc  |
| Emitter - Base Voltage         | $V_{EBO}$ | 6.0                 | Vdc  |
| Collector Current – Continuous | $I_C$     | 100                 | mAdc |
| Electrostatic Discharge        | HBM<br>MM | ESD<br>Class 2<br>B |      |

### THERMAL CHARACTERISTICS

| Characteristic (Single Heated)                                                                | Symbol          | Max            | Unit                       |
|-----------------------------------------------------------------------------------------------|-----------------|----------------|----------------------------|
| Total Device Dissipation $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ (Note 1) | $P_D$           | 240<br>1.9     | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient (Note 1)                                              | $R_{\theta JA}$ | 520            | $^\circ\text{C}/\text{W}$  |
| Total Device Dissipation $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ (Note 2) | $P_D$           | 280<br>2.2     | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient (Note 2)                                              | $R_{\theta JA}$ | 446            | $^\circ\text{C}/\text{W}$  |
| Characteristic (Dual Heated) (Note 3)                                                         | Symbol          | Max            | Unit                       |
| Total Device Dissipation $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ (Note 1) | $P_D$           | 350<br>2.8     | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient (Note 1)                                              | $R_{\theta JA}$ | 357            | $^\circ\text{C}/\text{W}$  |
| Total Device Dissipation $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ (Note 2) | $P_D$           | 420<br>3.4     | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient (Note 2)                                              | $R_{\theta JA}$ | 297            | $^\circ\text{C}/\text{W}$  |
| Junction and Storage Temperature Range                                                        | $T_J, T_{stg}$  | -55 to<br>+150 | $^\circ\text{C}$           |

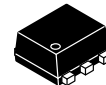
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
2. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.
3. Dual heated values assume total power is sum of two equally powered channels



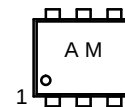
NST847BPDP6T5G\*

\* Q1 PNP  
Q2 NPN



SOT-963  
CASE 527AD

### MARKING DIAGRAM



A = Device Code  
M = Date Code

### ORDERING INFORMATION

| Device         | Package              | Shipping <sup>†</sup> |
|----------------|----------------------|-----------------------|
| NST847BPDP6T5G | SOT-963<br>(Pb-Free) | 8000/Tape & Reel      |

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

# NST847BPDP6T5G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C unless otherwise noted)

| Characteristic                                                                                                                                                                               | Symbol                                               | Min              | Typ              | Max                      | Unit                 |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------|------------------|------------------|--------------------------|----------------------|
| <b>OFF CHARACTERISTICS</b>                                                                                                                                                                   |                                                      |                  |                  |                          |                      |
| Collector - Emitter Breakdown Voltage<br>(I <sub>C</sub> = 1.0 mA, I <sub>B</sub> = 0)<br>(I <sub>C</sub> = -1.0 mA, I <sub>B</sub> = 0)                                                     | (NPN)<br>V <sub>(BR)CEO</sub><br>(PNP)               | 45<br>-45        | -<br>-           | -<br>-                   | V                    |
| Collector - Base Breakdown Voltage<br>(I <sub>C</sub> = 10 µA, I <sub>E</sub> = 0)<br>(I <sub>C</sub> = -10 µA, I <sub>E</sub> = 0)                                                          | (NPN)<br>V <sub>(BR)CBO</sub><br>(PNP)               | 50<br>-50        | -<br>-           | -<br>-                   | V                    |
| Collector - Emitter Breakdown Voltage<br>(I <sub>C</sub> = 10 µA)<br>(I <sub>C</sub> = -10 µA)                                                                                               | (NPN)<br>V <sub>(BR)CES</sub><br>(PNP)               | 50<br>-50        | -<br>-           | -<br>-                   | V                    |
| Emitter - Base Breakdown Voltage<br>(I <sub>E</sub> = 1.0 µA, I <sub>C</sub> = 0)<br>(I <sub>E</sub> = -1.0 µA, I <sub>C</sub> = 0)                                                          | (NPN)<br>V <sub>(BR)EBO</sub><br>(PNP)               | 6.0<br>-5.0      | -<br>-           | -<br>-                   | V                    |
| Collector Cutoff Current<br>(V <sub>CB</sub> = 30 V)<br>(V <sub>CB</sub> = 30 V, T <sub>A</sub> = 150 °C)<br>(V <sub>CB</sub> = -30 V)<br>(V <sub>CB</sub> = -30 V, T <sub>A</sub> = 150 °C) | (NPN)<br>I <sub>CBO</sub><br>(NPN)<br>(PNP)<br>(PNP) | -<br>-<br>-<br>- | -<br>-<br>-<br>- | 15<br>5.0<br>-15<br>-4.0 | nA<br>µA<br>nA<br>µA |

## ON CHARACTERISTICS (Note 4)

|                                                                                                                                                                                                                                                                      |                    |                      |                         |                                |                                |   |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------|----------------------|-------------------------|--------------------------------|--------------------------------|---|
| DC Current Gain<br>(I <sub>C</sub> = 2.0 mA, V <sub>CE</sub> = 5.0 V)<br><br>(I <sub>C</sub> = -2.0 mA, V <sub>CE</sub> = -5.0 V)                                                                                                                                    | (NPN)<br><br>(PNP) | h <sub>FE</sub>      | 200<br>220              | 290<br>290                     | 450<br>475                     | - |
| Collector - Emitter Saturation Voltage<br>(I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.5 mA)<br>(I <sub>C</sub> = 100 mA, I <sub>B</sub> = 5.0 mA)<br><br>(I <sub>C</sub> = -10 mA, I <sub>B</sub> = -0.5 mA)<br>(I <sub>C</sub> = -100 mA, I <sub>B</sub> = -5.0 mA) | (NPN)<br><br>(PNP) | V <sub>CE(sat)</sub> | -<br>-<br>-<br>-        | -<br>-<br>-<br>-               | 0.25<br>0.60<br>-0.30<br>-0.70 | V |
| Base - Emitter Saturation Voltage<br>(I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.5 mA)<br>(I <sub>C</sub> = 100 mA, I <sub>B</sub> = 5.0 mA)<br><br>(I <sub>C</sub> = -10 mA, I <sub>B</sub> = -0.5 mA)<br>(I <sub>C</sub> = -100 mA, I <sub>B</sub> = -5.0 mA)      | (NPN)<br><br>(PNP) | V <sub>BE(sat)</sub> | -<br>-<br>-<br>-        | 0.70<br>0.90<br>-0.70<br>-0.90 | -<br>-<br>-<br>-               | V |
| Base - Emitter On Voltage<br>(I <sub>C</sub> = 2.0 mA, V <sub>CE</sub> = 5.0 V)<br>(I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 V)<br><br>(I <sub>C</sub> = -2.0 mA, V <sub>CE</sub> = -5.0 V)<br>(I <sub>C</sub> = -10 mA, V <sub>CE</sub> = -5.0 V)              | (NPN)<br><br>(PNP) | V <sub>BE(on)</sub>  | 0.58<br>-<br>-0.60<br>- | 0.66<br>-<br>-<br>-            | 0.70<br>0.77<br>-0.75<br>-0.82 | V |

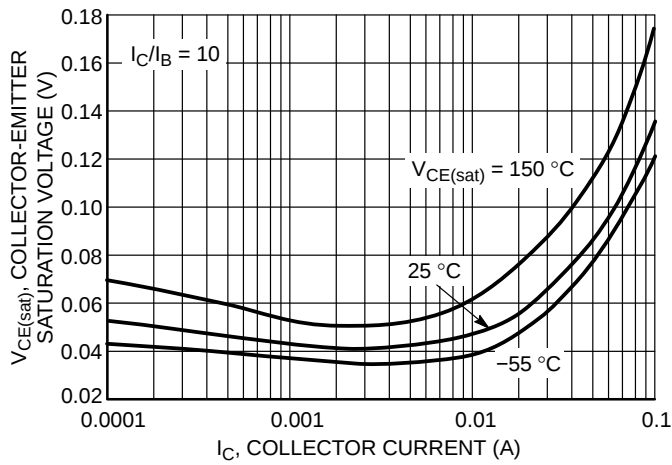
## SMALL-SIGNAL CHARACTERISTICS

|                                                                                                                                                                                                                              |                    |                 |            |        |            |     |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------|-----------------|------------|--------|------------|-----|
| Current-Gain – Bandwidth Product<br>(I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 V, f = 100 MHz)<br><br>(I <sub>C</sub> = -10 mA, V <sub>CE</sub> = -5.0 V, f = 100 MHz)                                                   | (NPN)<br><br>(PNP) | f <sub>T</sub>  | 100<br>100 | -<br>- | -<br>-     | MHz |
| Output Capacitance<br>(V <sub>CB</sub> = 10 V, f = 1.0 MHz)<br><br>(V <sub>CB</sub> = -10 V, f = 1.0 MHz)                                                                                                                    | (NPN)<br><br>(PNP) | C <sub>ob</sub> | -<br>-     | -<br>- | 4.5<br>4.5 | pF  |
| Noise Figure<br>(I <sub>C</sub> = 0.2 mA, V <sub>CE</sub> = 5.0 V, R <sub>S</sub> = 2 kΩ, f = 1 kHz, BW = 200 Hz)<br><br>(I <sub>C</sub> = -0.2 mA, V <sub>CE</sub> = -5.0 V, R <sub>S</sub> = 2 kΩ, f = 1 kHz, BW = 200 Hz) | (NPN)<br><br>(PNP) | NF              | -<br>-     | -<br>- | 10<br>10   | dB  |

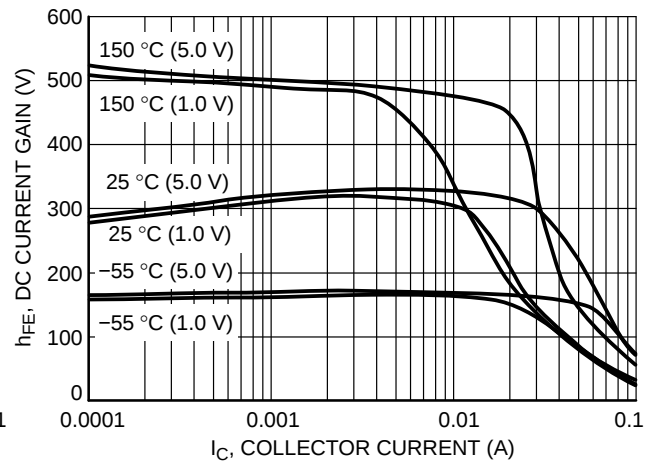
4. Pulse Test: Pulse Width ≤ 300 µs; Duty Cycle ≤ 2.0%.

# NST847BPDP6T5G

## NPN TRANSISTOR



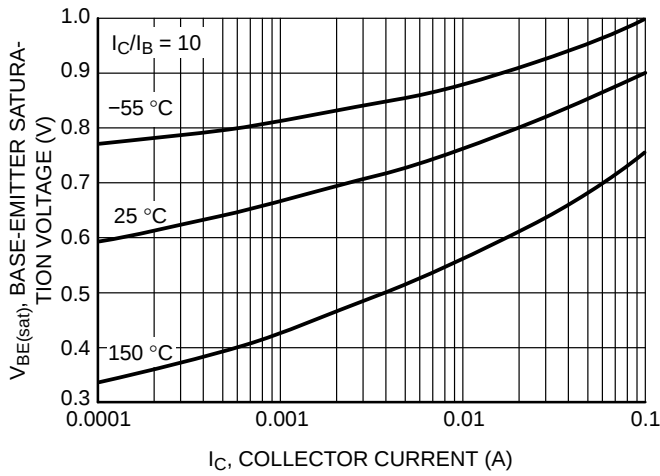
**Figure 1. Collector Emitter Saturation Voltage vs. Collector Current**



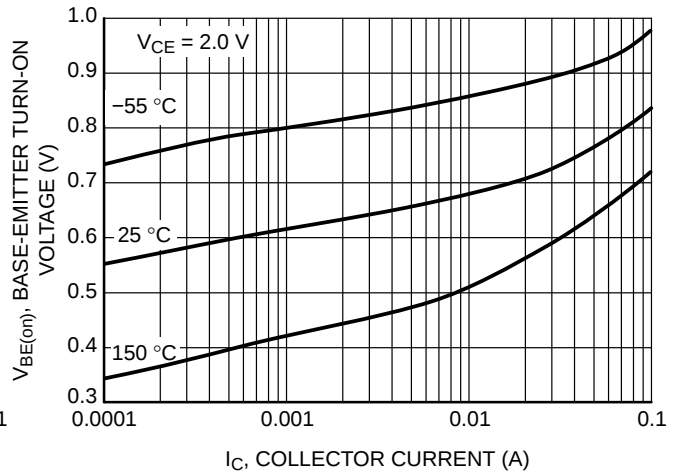
**Figure 2. DC Current Gain vs. Collector Current**

# NST847BPDP6T5G

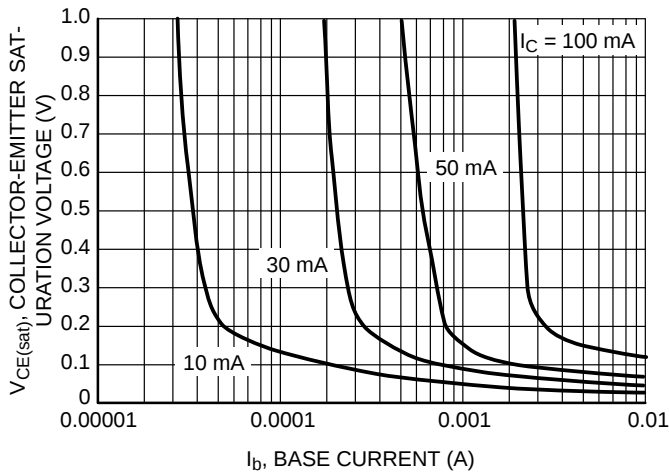
## NPN TRANSISTOR



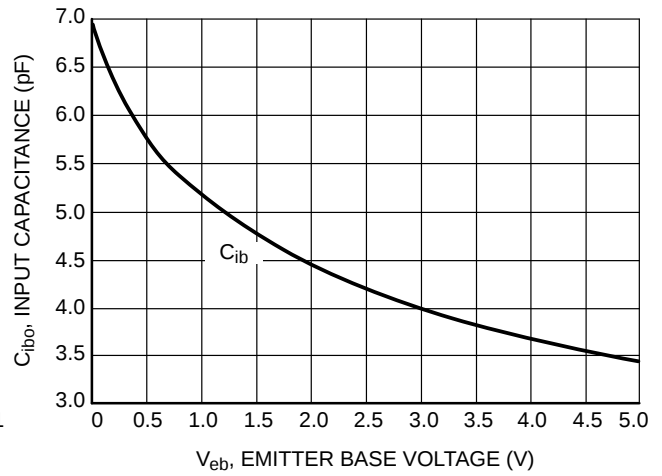
**Figure 3. Base Emitter Saturation Voltage vs. Collector Current**



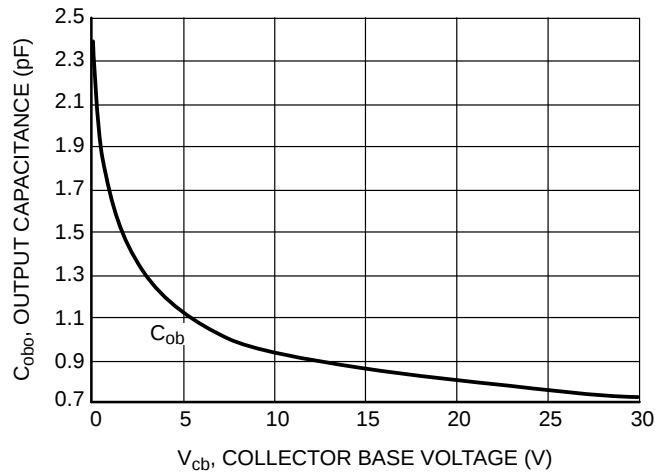
**Figure 4. Base Emitter Turn-On Voltage vs. Collector Current**



**Figure 5. Saturation Region**



**Figure 6. Input Capacitance**



**Figure 7. Output Capacitance**

PNP TRANSISTOR

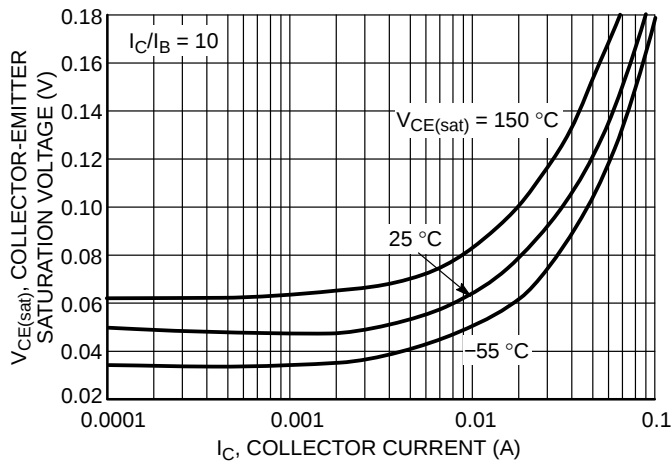


Figure 8. Collector Emitter Saturation Voltage vs. Collector Current

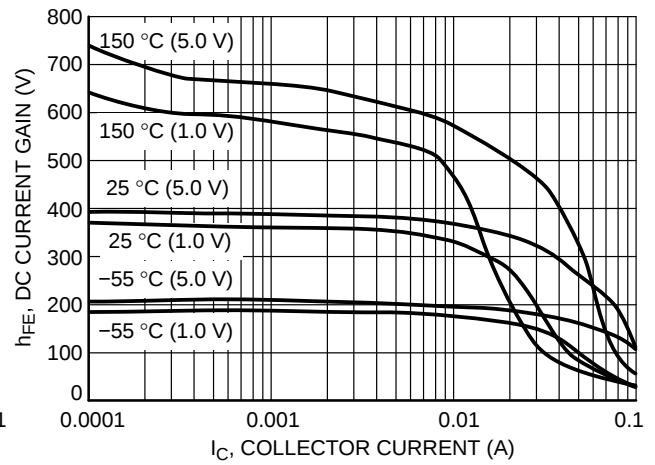


Figure 9. DC Current Gain vs. Collector Current

PNP TRANSISTOR

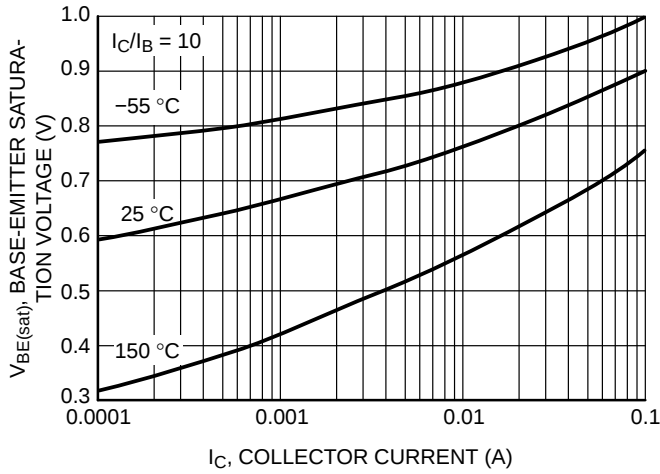


Figure 10. Base Emitter Saturation Voltage vs. Collector Current

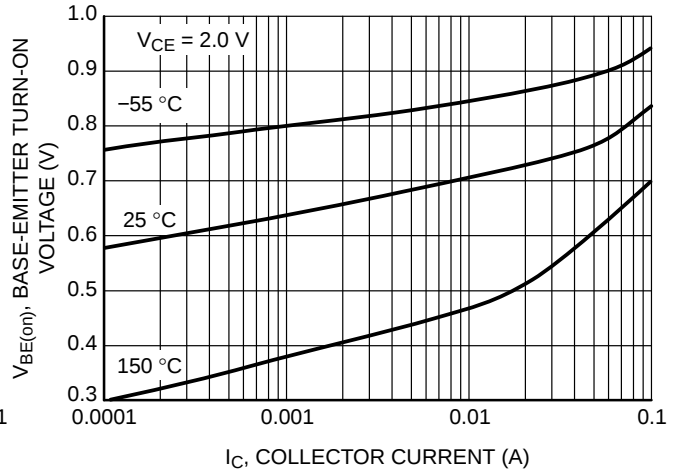


Figure 11. Base Emitter Turn-On Voltage vs. Collector Current

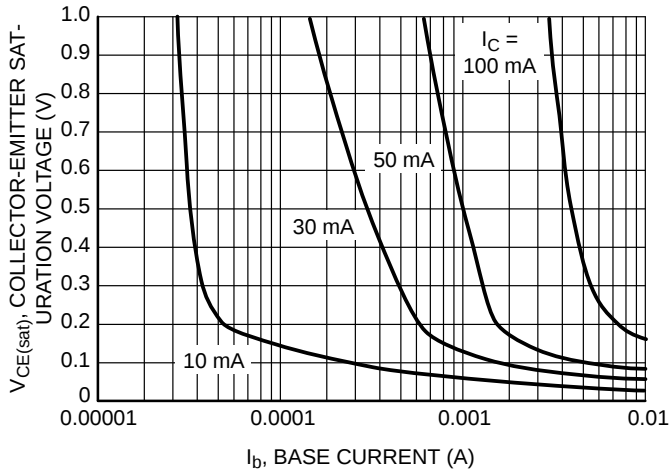


Figure 12. Saturation Region

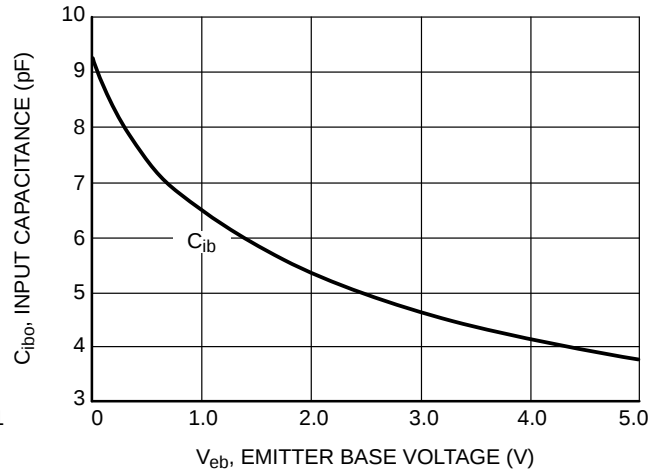


Figure 13. Input Capacitance

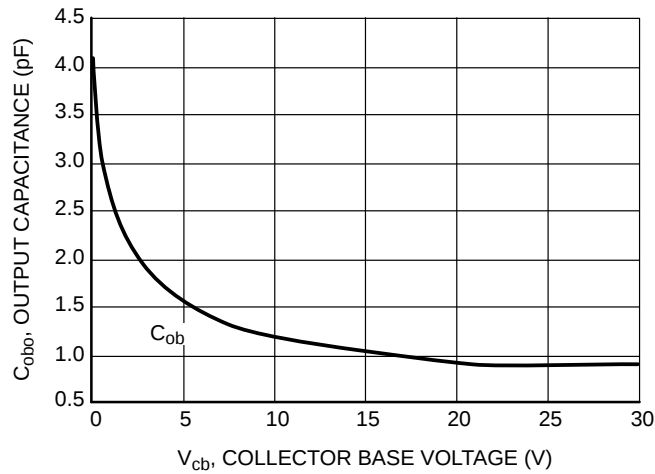
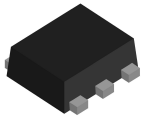


Figure 14. Output Capacitance

## NST847BPDP6T5G

### REVISION HISTORY

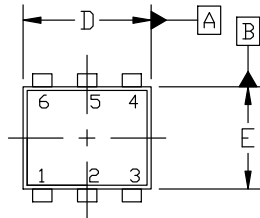
| Revision | Description of Changes                            | Date      |
|----------|---------------------------------------------------|-----------|
| 2        | Rebranded the Data Sheet to <b>onsemi</b> format. | 6/25/2025 |


**SOT-963 1.00x1.00x0.37, 0.35P**  
**CASE 527AD**  
**ISSUE F**

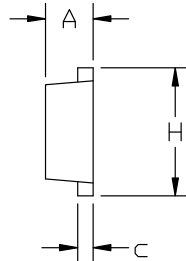
DATE 20 FEB 2024

## NOTES:

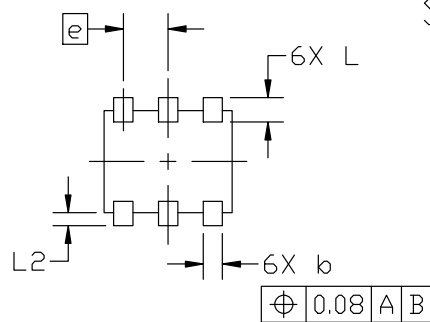
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



TOP VIEW

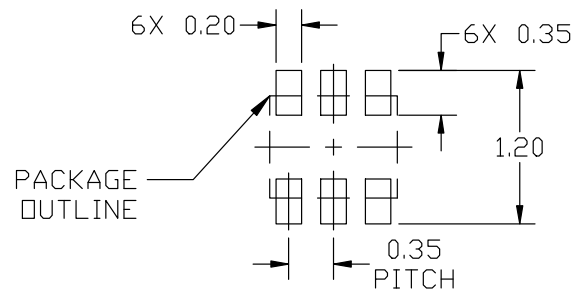


SIDE VIEW



BOTTOM VIEW

| DIM | MILLIMETERS |      |      |
|-----|-------------|------|------|
|     | MIN.        | NOM. | MAX. |
| A   | 0.34        | 0.37 | 0.40 |
| b   | 0.10        | 0.15 | 0.20 |
| c   | 0.07        | 0.12 | 0.17 |
| D   | 0.95        | 1.00 | 1.05 |
| E   | 0.75        | 0.80 | 0.85 |
| e   | 0.35 BSC    |      |      |
| H   | 0.95        | 1.00 | 1.05 |
| L   | 0.19 REF    |      |      |
| L2  | 0.05        | 0.10 | 0.15 |


RECOMMENDED MOUNTING  
FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

## STYLE 1:

- PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

## STYLE 2:

- PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

## STYLE 3:

- PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

## STYLE 4:

- PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

## STYLE 5:

- PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

## STYLE 6:

- PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

## STYLE 7:

- PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

## STYLE 8:

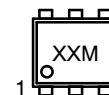
- PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

## STYLE 9:

- PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

## STYLE 10:

- PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

**GENERIC  
MARKING DIAGRAM\***


XX = Specific Device Code  
M = Month Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

|                         |                                      |                                                                                                                                                                                  |
|-------------------------|--------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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| <b>DESCRIPTION:</b>     | <b>SOT-963 1.00x1.00x0.37, 0.35P</b> | <b>PAGE 1 OF 1</b>                                                                                                                                                               |

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